

## Silicon NPN Power Transistors

2SC1826

## DESCRIPTION

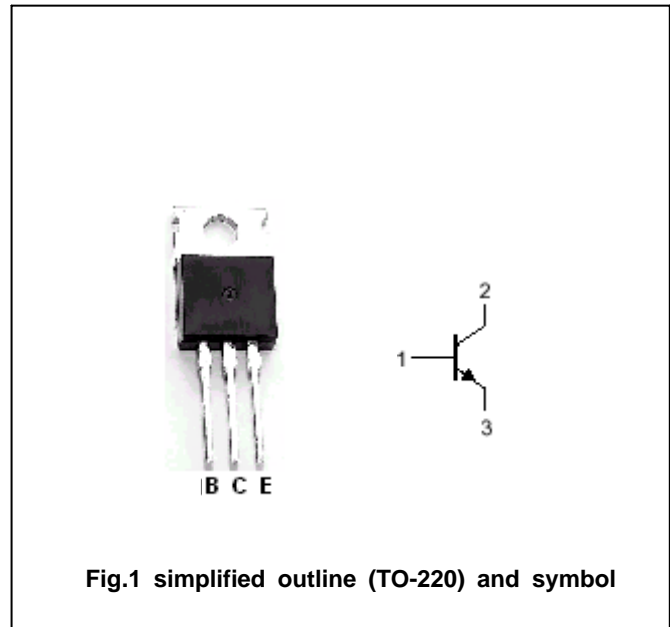
- With TO-220 package
- Collector current : $I_C=4A$
- Collector power dissipation  
: $P_C=30W@T_C=25^\circ C$

## APPLICATIONS

- For use in low frequency power amplifier applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings ( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	80	V
$V_{CEO}$	Collector-emitter voltage	Open base	60	V
$V_{EBO}$	Emitter-base voltage	Open collector	6	V
$I_C$	Collector current (DC)		4	A
$P_C$	Collector power dissipation	$T_C=25^\circ C$	30	W
$T_j$	Junction temperature		150	$^\circ C$
$T_{stg}$	Storage temperature		-55~150	$^\circ C$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =25mA ; I <sub>B</sub> =0	60			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA ; I <sub>E</sub> =0	80			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA ; I <sub>C</sub> =0	6			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =3A ; I <sub>B</sub> =0.3A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =3A ; I <sub>B</sub> =0.3A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =80V ; I <sub>E</sub> =0			100	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =6V ; I <sub>C</sub> =0			100	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =4V	40		320	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =12V		10		MHz

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PACKAGE OUTLINE

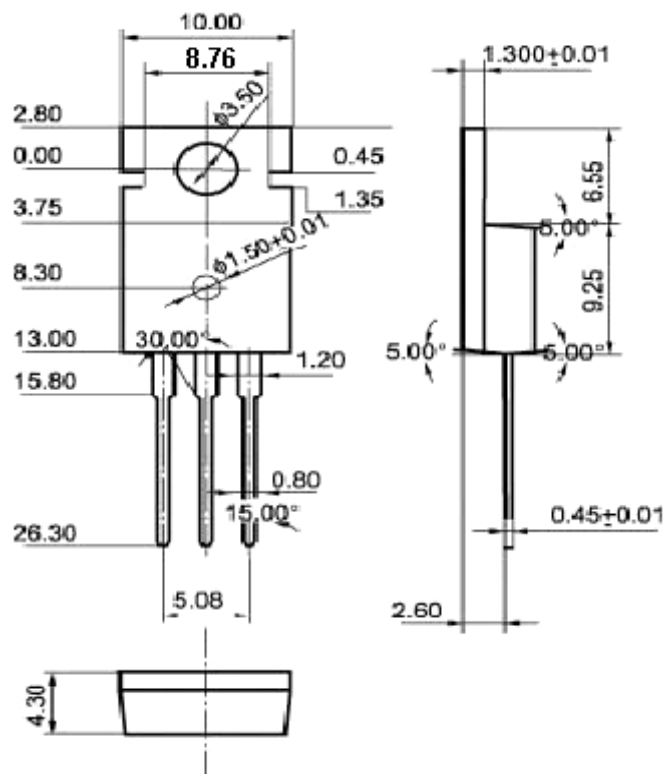


Fig.2 outline dimensions (unindicated tolerance:  $\pm 0.10$  mm)